

Notice of References CitedApplication/Control No.
09/498,303Applicant(s)/Patent Under
Reexamination
HAN ET AL.Examiner
Roberts CulbertArt Unit
1763

Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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NON-PATENT DOCUMENTS

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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
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